

# PMEG3050BEP

# 5 A low V<sub>F</sub> MEGA Schottky barrier rectifier Rev. 01 — 28 October 2009

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features

- Average forward current: I<sub>F(AV)</sub> ≤ 5 A
- Reverse voltage: V<sub>R</sub> ≤ 30 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

#### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 1. Quick reference data  $T_i = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	square wave; $\delta$ = 0.5; f = 20 kHz; $T_{sp} \le 135$ °C	-	-	5	Α
$V_R$	reverse voltage		-	-	30	V
$V_{F}$	forward voltage	I <sub>F</sub> = 5 A	-	400	450	mV
$I_R$	reverse current	$V_{R} = 30 \text{ V}$	-	90	250	μΑ



# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	. [4]
2	anode	1 2	1 1 2
		<u> </u>	sym001

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package	
	Name	Description	Version
PMEG3050BEP	-	plastic surface-mounted package; 2 leads	SOD128

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3050BEP	A8

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage	$T_j = 25  ^{\circ}C$	-	30	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5$ ; f = 20  kHz			
		$T_{amb} \le 20  ^{\circ}C$	<u>[1]</u> _	5	Α
		$T_{sp} \le 135  ^{\circ}C$	-	5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$	[2] _	70	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[3][4]	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2]  $T_i = 25$  °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
· · iii(j-a)	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3]	-	200	K/W
			<u>[4]</u> -	-	120	K/W
			<u>[5]</u> _	-	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [6] Soldering point of cathode tab.

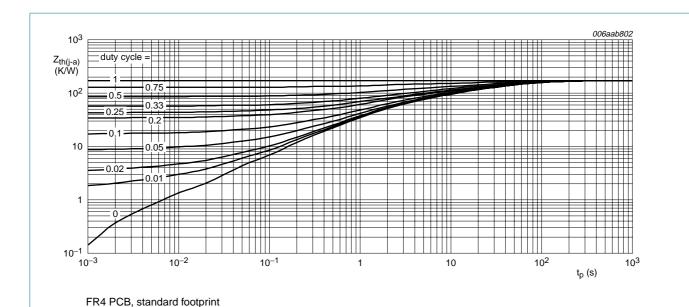
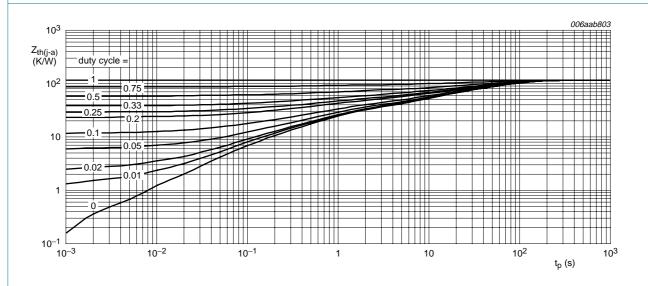
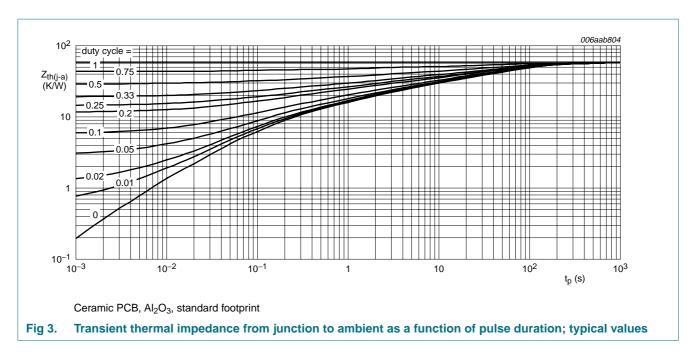


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

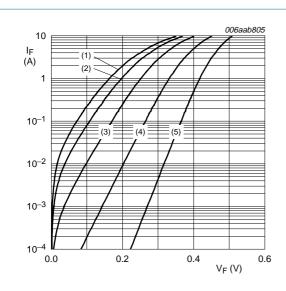


#### 7. **Characteristics**

Table 7. **Characteristics** 

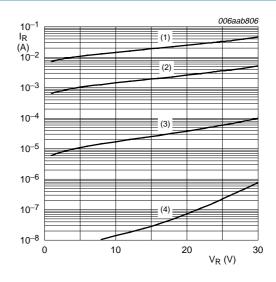
 $T_i = 25 \,^{\circ}C$  unless otherwise specified.

$\begin{array}{c} V_F \\ \\ V_F \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$V_{F}$	forward voltage	$I_F = 0.1 A$	-	270	300	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_F = 0.5 A$	-	315	360	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			I <sub>F</sub> = 1 A	-	335	380	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_F = 2 A$	-	360	420	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_F = 3 A$	-	380	440	mV
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_F = 5 A$	-	400	450	mV
$V_{R} = 30 \text{ V} \qquad - \qquad 90 \qquad 250 \qquad \mu A$ $C_{d} \qquad \text{diode capacitance} \qquad f = 1 \text{ MHz}$ $V_{R} = 1 \text{ V} \qquad - \qquad 800 \qquad - \qquad pF$	I <sub>R</sub> reverse current	reverse current	$V_R = 5 V$	-	10	-	μΑ
$C_d$ diode capacitance $f$ = 1 MHz $V_R$ = 1 $V$ - 800 - $pF$			$V_R = 10 V$	-	15	-	μΑ
V <sub>R</sub> = 1 V - 800 - pF			$V_R = 30 \text{ V}$	-	90	250	μΑ
···	C <sub>d</sub> diode capacitance		f = 1 MHz				
$V_{P} = 10 \text{ V}$ - 275 - pF			V <sub>R</sub> = 1 V	-	800	-	pF
K 2 1			V <sub>R</sub> = 10 V	-	275	-	pF



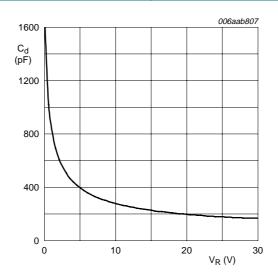
- (1)  $T_j = 150 \,^{\circ}\text{C}$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \,^{\circ}C$
- (4)  $T_j = 25 \,{}^{\circ}C$
- (5)  $T_i = -40 \, ^{\circ}\text{C}$

Fig 4. Forward current as a function of forward voltage; typical values



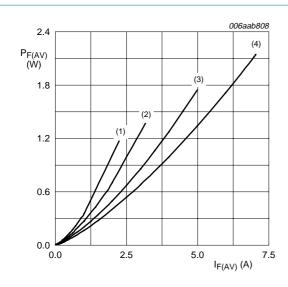
- (1) T<sub>j</sub> = 125 °C
- (2)  $T_j = 85 \,^{\circ}C$
- (3)  $T_j = 25 \,^{\circ}C$
- (4)  $T_j = -40 \, ^{\circ}C$

Fig 5. Reverse current as a function of reverse voltage; typical values



f = 1 MHz; T<sub>amb</sub> = 25 °C

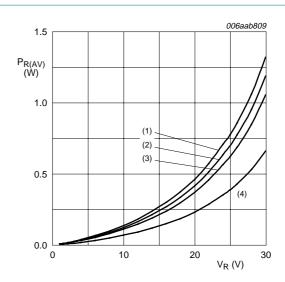
Fig 6. Diode capacitance as a function of reverse voltage; typical values



T<sub>j</sub> = 150 °C

- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

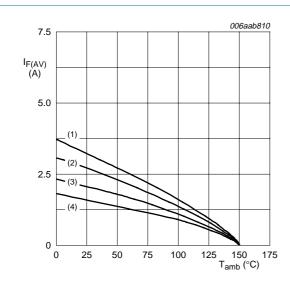
Average forward power dissipation as a Fig 7. function of average forward current; typical values



T<sub>i</sub> = 125 °C

- (1)  $\delta = 1$
- (2)  $\delta = 0.9$
- (3)  $\delta = 0.8$
- (4)  $\delta = 0.5$

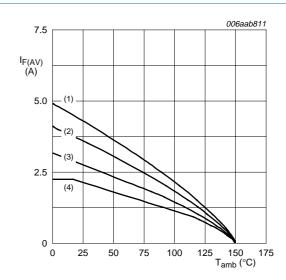
Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

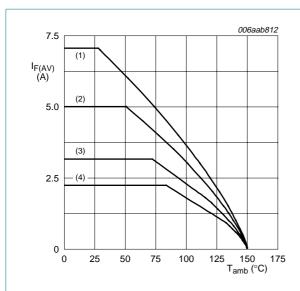
$$T_j = 150 \, ^{\circ}C$$

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values

# PMEG3050BEP

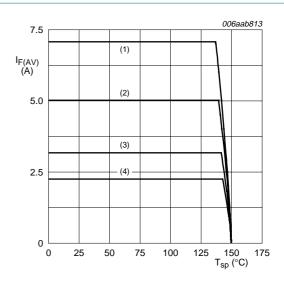
#### 5 A low V<sub>F</sub> MEGA Schottky barrier rectifier



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values

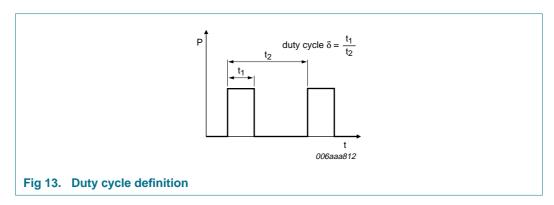


T<sub>j</sub> = 150 °C

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

## 8. Test information



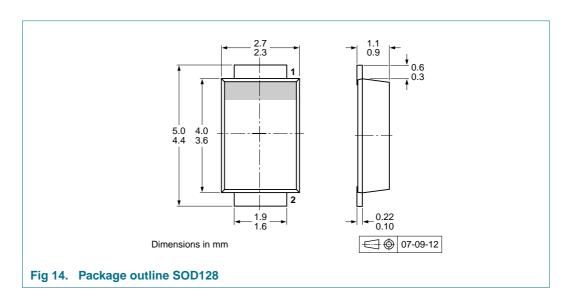
The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,

 $I_{RMS}=I_{F(AV)}$  at DC, and  $I_{RMS}=I_{M} imes\sqrt{\delta}$  with I<sub>RMS</sub> defined as RMS current.

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



# 10. Packing information

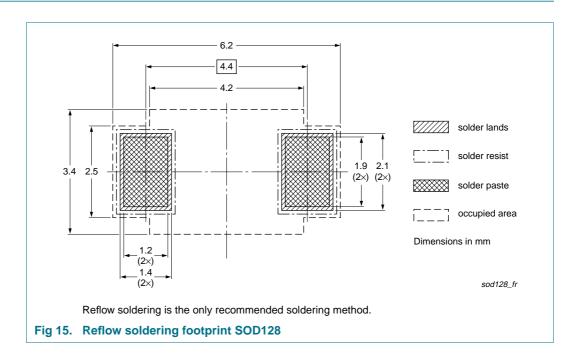
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PMEG3050BEP	SOD128	4 mm pitch, 12 mm tape and reel	-115

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

# 11. Soldering





# 12. Revision history

#### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3050BEP_1	20091028	Product data sheet	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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